

# MC74VHC245

## Octal Bus Buffer/Line Driver

The MC74VHC245 is an advanced high speed CMOS octal bus transceiver fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

It is intended for two-way asynchronous communication between data buses. The direction of data transmission is determined by the level of the DIR input. The output enable pin ( $\overline{OE}$ ) can be used to disable the device, so that the buses are effectively isolated.

All inputs are equipped with protection circuits against static discharge.

- High Speed:  $t_{PD} = 4.0$  ns (Typ) at  $V_{CC} = 5$  V
- Low Power Dissipation:  $I_{CC} = 4$   $\mu$ A (Max) at  $T_A = 25^\circ$ C
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\%$   $V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise:  $V_{OLP} = 1.2$  V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 308 FETs or 77 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant

### APPLICATION NOTES

- Do not force a signal on an I/O pin when it is an active output, damage may occur.
- All floating (high impedance) input or I/O pins must be fixed by means of pull up or pull down resistors or bus terminator ICs.
- A parasitic diode is formed between the bus and  $V_{CC}$  terminals. Therefore, the VHC245 cannot be used to interface 5 V to 3 V systems directly.



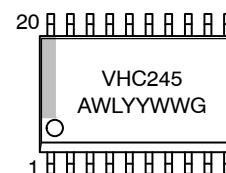
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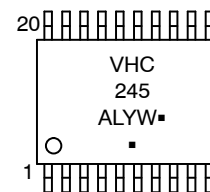
### MARKING DIAGRAMS



SOIC-20  
DW SUFFIX  
CASE 751D



TSSOP-20  
DT SUFFIX  
CASE 948E



VHC245 = Specific Device Code  
A = Assembly Location  
WL, L = Wafer Lot  
Y = Year  
WW, W = Work Week  
G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
MC74VHC245DWG	SOIC-20	38 Units/Rail
MC74VHC245DTG	TSSOP-20	75 Units/Rail
MC74VHC245DWR2G	SOIC-20	1000 Units/Reel
MC74VHC245DTR2G	TSSOP-20	2500 Units/T&R

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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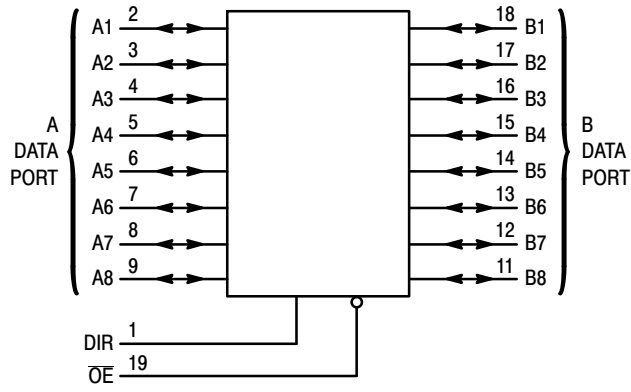


Figure 1. LOGIC DIAGRAM

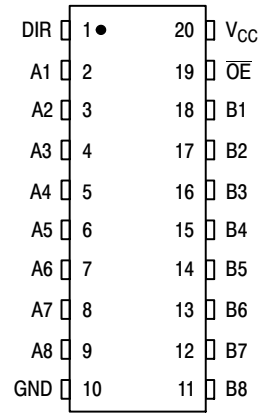


Figure 2. PIN ASSIGNMENT

## FUNCTION TABLE

Control Inputs		Operation
$\overline{OE}$	DIR	
L	L	Data Transmitted from Bus B to Bus A
L	H	Data Transmitted from Bus A to Bus B
H	X	Buses Isolated (High-Impedance State)

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## MAXIMUM RATINGS\*

Symbol	Parameter	Value	Unit	
V <sub>CC</sub>	DC Supply Voltage	- 0.5 to + 7.0	V	
V <sub>in</sub>	DC Input Voltage	- 0.5 to + 7.0	V	
V <sub>out</sub>	DC Output Voltage	- 0.5 to V <sub>CC</sub> + 0.5	V	
I <sub>IK</sub>	Input Diode Current	- 20	mA	
I <sub>OK</sub>	Output Diode Current	± 20	mA	
I <sub>out</sub>	DC Output Current, per Pin	± 25	mA	
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	± 75	mA	
P <sub>D</sub>	Power Dissipation in Still Air	SOIC Packages† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C	

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V<sub>in</sub> and V<sub>out</sub> should be constrained to the range GND ≤ (V<sub>in</sub> or V<sub>out</sub>) ≤ V<sub>CC</sub>. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

\* Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

† Derating — SOIC Packages: - 7 mW/°C from 65° to 125°C  
TSSOP Package: - 6.1 mW/°C from 65° to 125°C

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	2.0	5.5	V
V <sub>in</sub>	DC Input Voltage	0	5.5	V
V <sub>out</sub>	DC Output Voltage	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature	- 40	+ 85	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time	V <sub>CC</sub> = 3.3V ± 0.3V V <sub>CC</sub> = 5.0V ± 0.5V	0 100 20	ns/V

## DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	T <sub>A</sub> = 25°C			T <sub>A</sub> = - 40 to 85°C		Unit
				Min	Typ	Max	Min	Max	
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0 3.0 to 5.5	1.50 V <sub>CC</sub> × 0.7			1.50 V <sub>CC</sub> × 0.7		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0 3.0 to 5.5			0.50 V <sub>CC</sub> × 0.3		0.50 V <sub>CC</sub> × 0.3	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OH</sub> = - 50μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V
		V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OH</sub> = - 4mA I <sub>OH</sub> = - 8mA	3.0 4.5	2.58 3.94			2.48 3.80		
V <sub>OL</sub>	Maximum Low-Level Output Voltage	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OL</sub> = 50μA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V
		V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OL</sub> = 4mA I <sub>OL</sub> = 8mA	3.0 4.5			0.36 0.36		0.44 0.44	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = 5.5 V or GND (DIR, OE)	0 to 5.5			± 0.1		± 1.0	μA

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## DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	T <sub>A</sub> = 25°C			T <sub>A</sub> = - 40 to 85°C		Unit
				Min	Typ	Max	Min	Max	
I <sub>OZ</sub>	Maximum Three-State Leakage Current	V <sub>in</sub> = V <sub>IL</sub> or V <sub>IH</sub> V <sub>out</sub> = V <sub>CC</sub> or GND	5.5			± 0.25		± 2.5	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current	V <sub>in</sub> = V <sub>CC</sub> or GND	5.5			4.0		40.0	μA

## AC ELECTRICAL CHARACTERISTICS (Input t<sub>r</sub> = t<sub>f</sub> = 3.0ns)

Symbol	Parameter	Test Conditions	T <sub>A</sub> = 25°C			T <sub>A</sub> = - 40 to 85°C		Unit
			Min	Typ	Max	Min	Max	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, A to B or B to A	V <sub>CC</sub> = 3.3 ± 0.3V C <sub>L</sub> = 15pF		5.8	8.4	1.0	10.0	ns
		C <sub>L</sub> = 50pF		8.3	11.9	1.0	13.5	
		V <sub>CC</sub> = 5.0 ± 0.5V C <sub>L</sub> = 15pF		4.0	5.5	1.0	6.5	
		C <sub>L</sub> = 50pF		5.5	7.5	1.0	8.5	
t <sub>PZL</sub> , t <sub>PZH</sub>	Output Enable Time OE to A or B	V <sub>CC</sub> = 3.3 ± 0.3V C <sub>L</sub> = 15pF		8.5	13.2	1.0	15.5	ns
		R <sub>L</sub> = 1 kΩ C <sub>L</sub> = 50pF		11.0	16.7	1.0	19.0	
		V <sub>CC</sub> = 5.0 ± 0.5V C <sub>L</sub> = 15pF		5.8	8.5	1.0	10.0	
		R <sub>L</sub> = 1 kΩ C <sub>L</sub> = 50pF		7.3	10.6	1.0	12.0	
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Output Disable Time OE to A or B	V <sub>CC</sub> = 3.3 ± 0.3V C <sub>L</sub> = 50pF		11.5	15.8	1.0	18.0	ns
		R <sub>L</sub> = 1 kΩ						
		V <sub>CC</sub> = 5.0 ± 0.5V C <sub>L</sub> = 50pF		7.0	9.7	1.0	11.0	
		R <sub>L</sub> = 1 kΩ						
t <sub>OSLH</sub> , t <sub>OSHL</sub>	Output to Output Skew	V <sub>CC</sub> = 3.3 ± 0.3V C <sub>L</sub> = 50pF			1.5		1.5	ns
		(Note 1)						
		V <sub>CC</sub> = 5.0 ± 0.5V C <sub>L</sub> = 50pF			1.0		1.0	ns
		(Note 1)						
C <sub>in</sub>	Maximum Input Capacitance DIR, OE			4	10		10	pF
C <sub>I/O</sub>	Maximum Three-State I/O Capacitance			8				pF

C <sub>PD</sub>	Power Dissipation Capacitance (Note 2)	Typical @ 25°C, V <sub>CC</sub> = 5.0V		pF
		Min	Max	
			21	

- Parameter guaranteed by design. t<sub>OSLH</sub> = |t<sub>PLHm</sub> - t<sub>PLHn</sub>|, t<sub>OSHL</sub> = |t<sub>PHLm</sub> - t<sub>PHLn</sub>|.
- C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub> / 8 (per bit). C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

## NOISE CHARACTERISTICS (Input t<sub>r</sub> = t<sub>f</sub> = 3.0ns, C<sub>L</sub> = 50pF, V<sub>CC</sub> = 5.0V)

Symbol	Parameter	T <sub>A</sub> = 25°C		Unit
		Typ	Max	
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.9	1.2	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.9	-1.2	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		3.5	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		1.5	V



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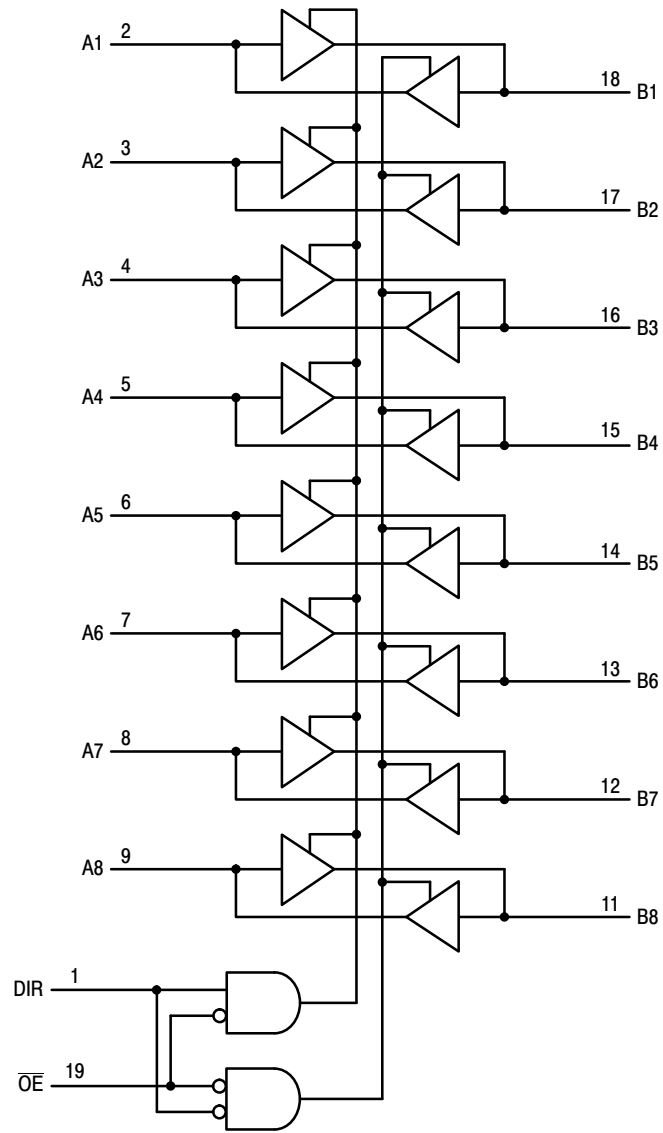


Figure 7. EXPANDED LOGIC DIAGRAM

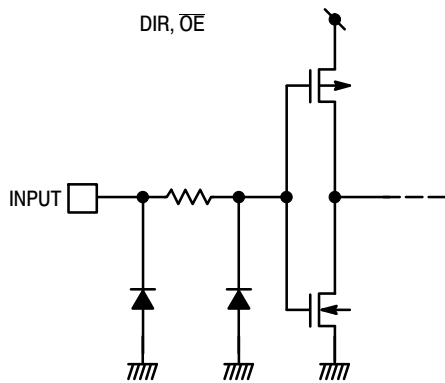


Figure 8. INPUT EQUIVALENT CIRCUIT

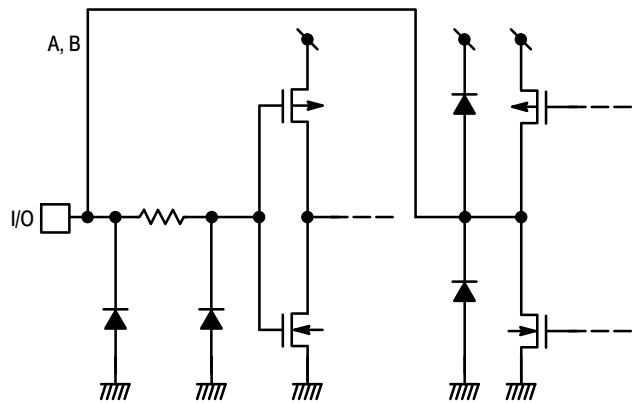


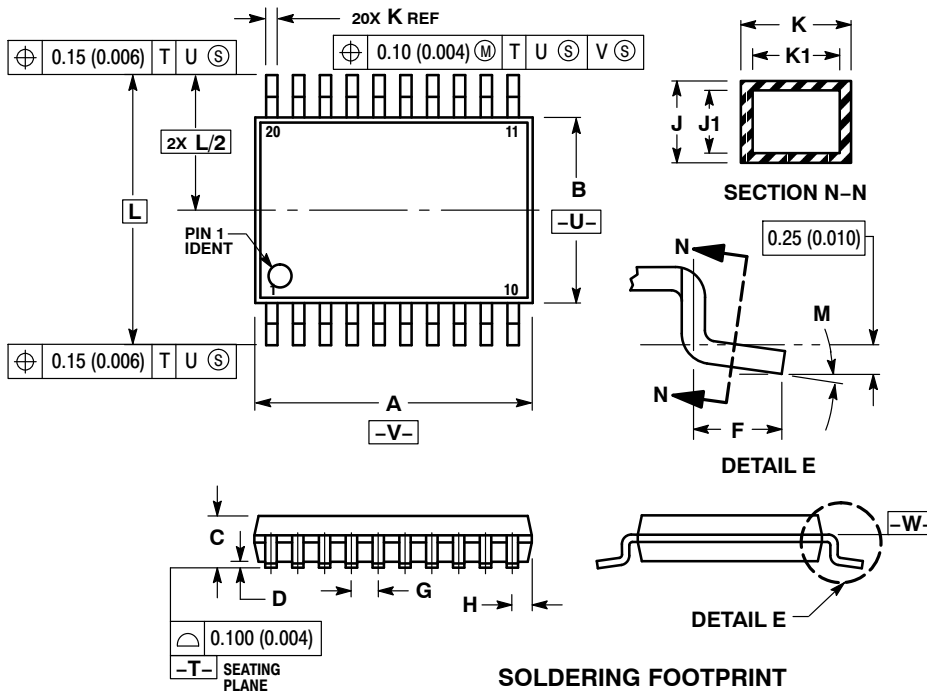
Figure 9. BUS TERMINAL EQUIVALENT CIRCUIT



# MC74VHC245

## PACKAGE DIMENSIONS

TSSOP-20  
CASE 948E-02  
ISSUE C

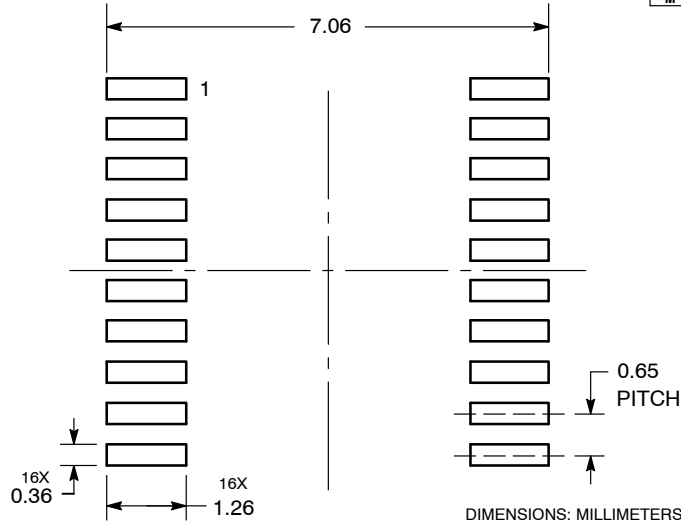


### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	6.40	6.60	0.252	0.260
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

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- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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